S2M040150BJ

TriQSiC™ 1500V Silicon C

2 Electrical characteristics

2.1 Static characteristics

Table 4 Static characteristics (Tc = 25°C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-source breakdown voltage	1500	-	-	V	V_{GS} = 0V, I_D = 100μA	
$V_{GS(th)}$	Gate threshold voltage	2.3	2.8	3.6	V	V_{DS} = V_{GS}, I_D = 10mA	Fig.11
		-	2.0	-	V	V_{DS} = V_{GS}, I_D = 10mA T_J = 175°C	
I_{DSS}	Zero gate voltage drain current	-	1	10	μA	V_{DS} = 1500V, V_{GS} = 0V	
I_{GSS}	Gate source leakage current	-	-	100	nA	V_{GS} = 18V, V_{DS} = 0V	
$R_{DS(on)}$	Current drain-source on-state						

3 Electrical characteristic diagrams

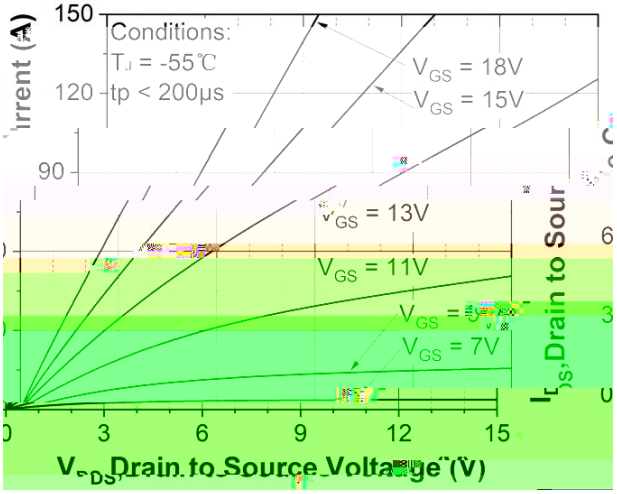


Figure 1. Output characteristics T_J = -55 ºC

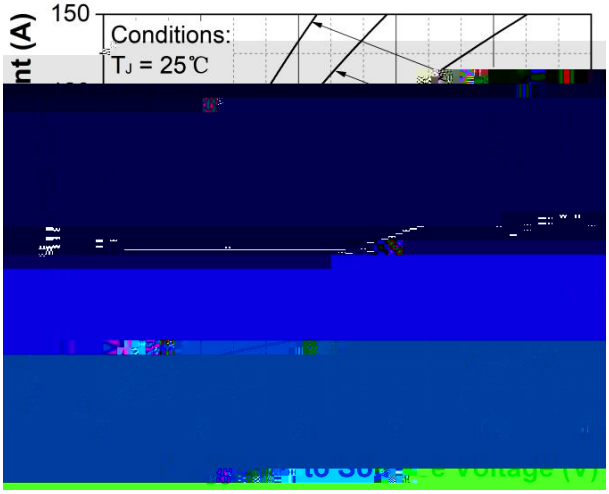


Figure 2. Output characteristics T_J = 25 ºC

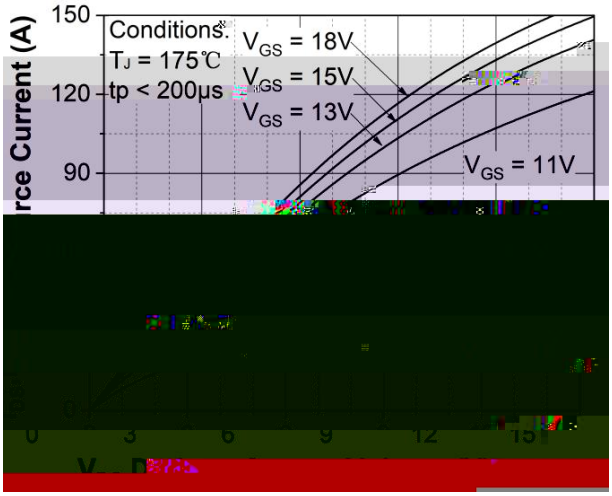


Figure 3. Output characteristics T_J = 175 ºC

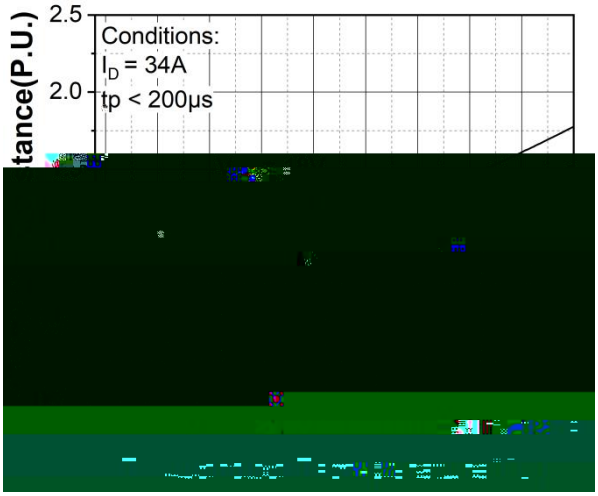


Figure 4. Normalized on-resistance vs. temperature

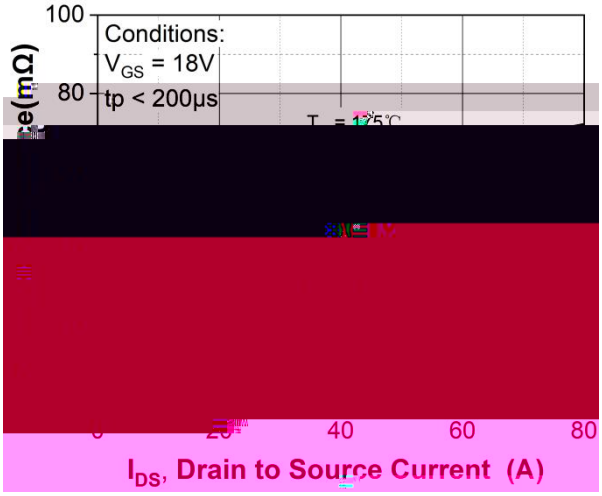


Figure 5. On-resistance vs. drain current for various temperatures

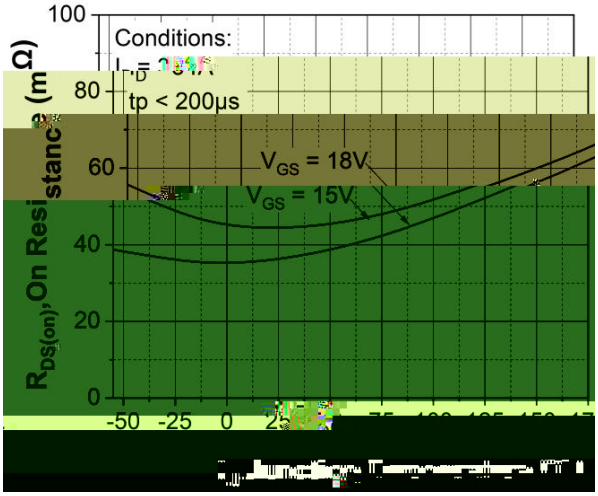


Figure 6. On-resistance vs. temperature for various gate voltages

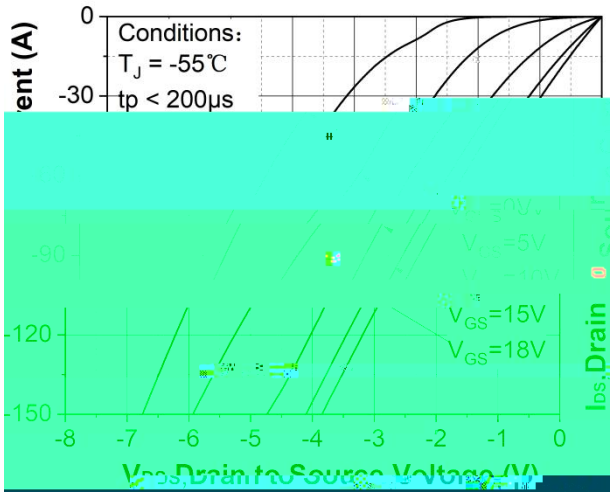


Figure 13. 3rd quadrant characteristic at T_J = -55 ºC

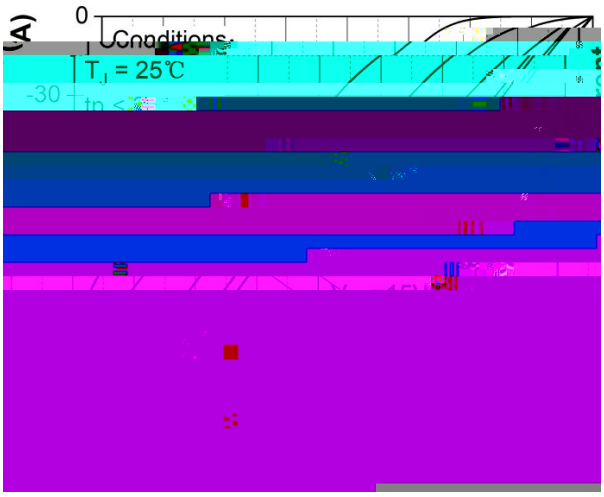


Figure 14. 3rd quadrant characteristic at T_J = 25 ºC

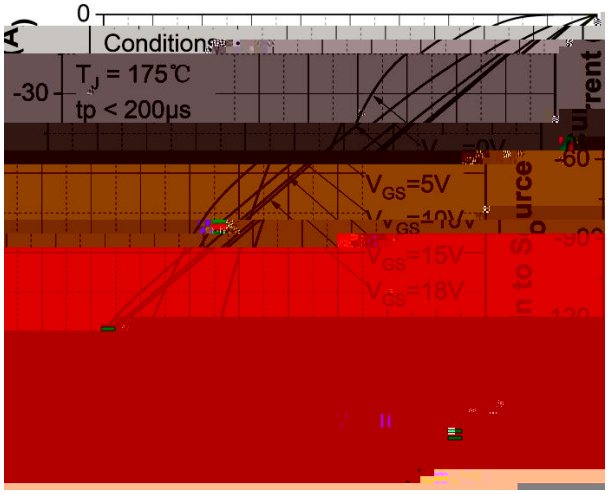


Figure 15. 3rd quadrant characteristic at T_J = 175 ºC

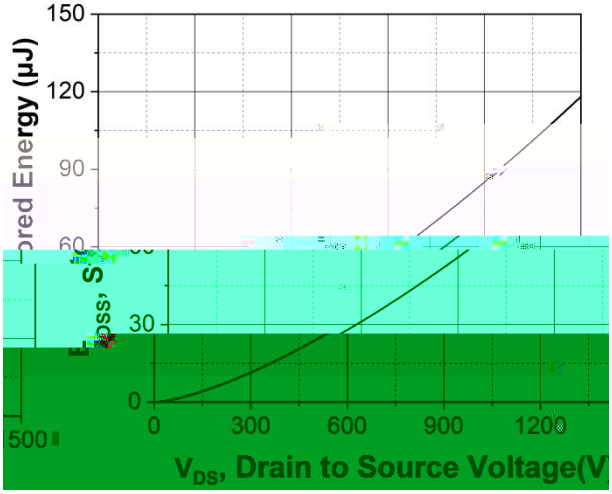


Figure 16. Output capacitor stored energy

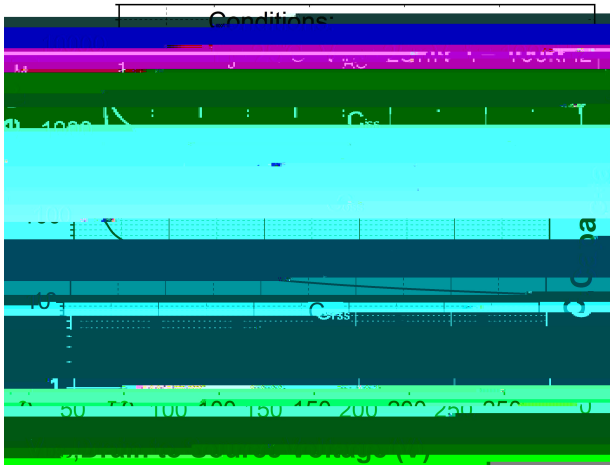


Figure 17. Capacitances vs. drain-source voltage (0 - 250V)

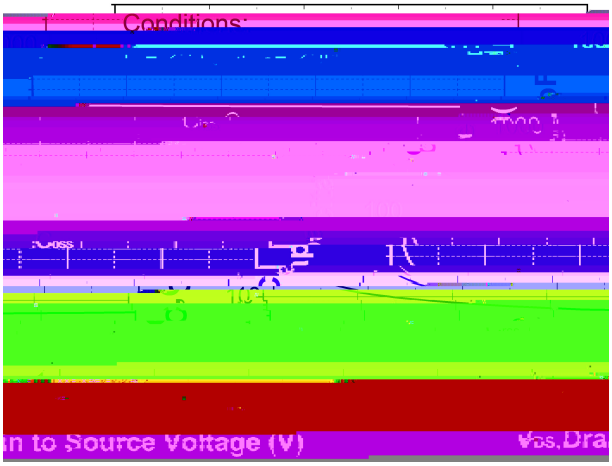


Figure 18. Capacitances vs. drain-source voltage (0 - 1500V)

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S2M04015 0

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